

PBSS302ND

40 V NPN low V_{CEsat} (BISS) transistor

Rev. 01 — 19 April 2005

Product data sheet

1. Product profile

1.1 General description

NPN low V_{CEsat} Breakthrough in Small Signal (BISS) transistor in a SOT457 (SC-74) SMD plastic package.

PNP complement: PBSS302PD.

1.2 Features

- Ultra low collector-emitter saturation voltage V_{CEsat}
- 4 A continuous collector current capability I_C (DC)
- Up to 15 A peak current
- Very low collector-emitter saturation resistance
- High efficiency due to less heat generation

1.3 Applications

- Power management functions
- Charging circuits
- DC-to-DC conversion
- MOSFET gate driving
- Power switches (e.g. motors, fans)
- Thin Film Transistor (TFT) backlight inverter

1.4 Quick reference data

Table 1: Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	40	V
I_C	collector current (DC)		[1]	-	4	A
I_{CM}	peak collector current	$t = 1$ ms or limited by $T_{j(max)}$	-	-	15	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = 6$ A; $I_B = 600$ mA	[2]	55	75	m Ω

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), AL_2O_3 , standard footprint.

[2] Pulse test: $t_p \leq 300$ μ s; $\delta \leq 0.02$.

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2. Pinning information

Table 2: Pinning

Pin	Description	Simplified outline	Symbol
1	collector		 sym014
2	collector		
3	base		
4	emitter		
5	collector		
6	collector		

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
PBSS302ND	SC-74	plastic surface mounted package; 6 leads	SOT457

4. Marking

Table 4: Marking codes

Type number	Marking code
PBSS302ND	C7

5. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

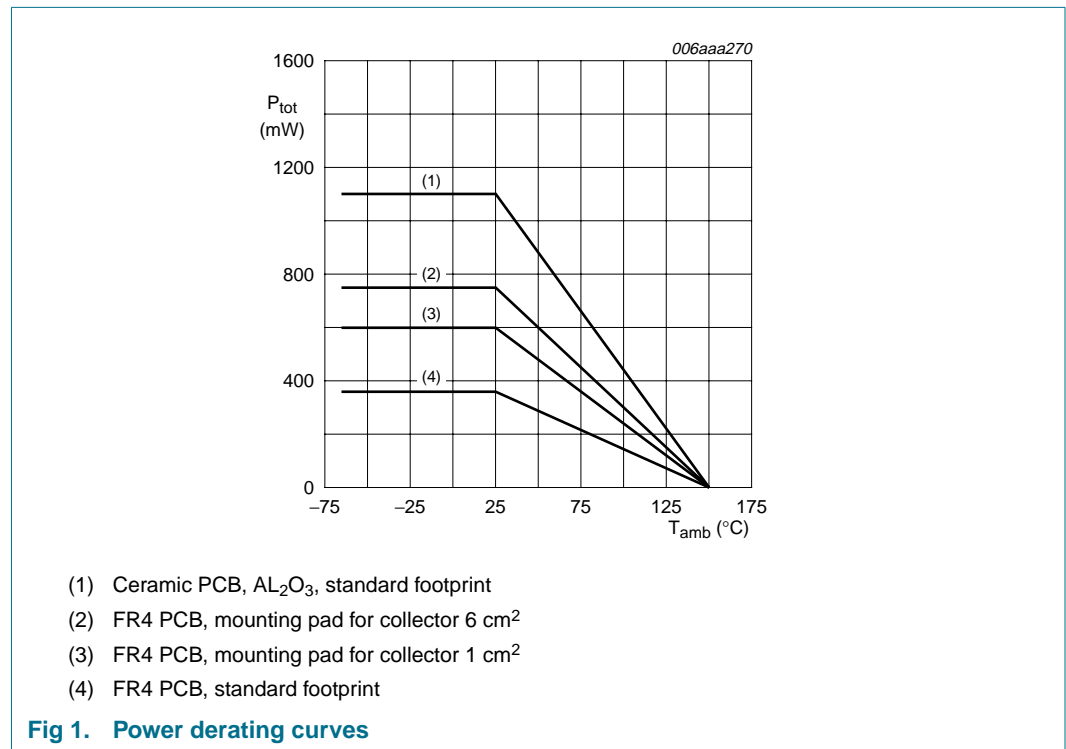
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	60	V
V_{CEO}	collector-emitter voltage	open base	-	40	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
I_C	collector current (DC)		[1]	4	A
I_{CM}	peak collector current	$t = 1$ ms or limited by $T_{j(max)}$	-	15	A
I_B	base current (DC)		-	0.8	A
I_{BM}	peak base current	$t_p \leq 300$ μ s	-	2	A
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[2]	360	mW
			[3]	600	mW
			[4]	750	mW
			[1]	1.1	W
			[2] [5]	2.5	W

Table 5: Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	+150	°C

- [1] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm^2 .
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm^2 .
- [5] Operated under pulsed conditions: Duty cycle $\delta \leq 10\%$ and pulse width $t_p \leq 10\text{ ms}$.

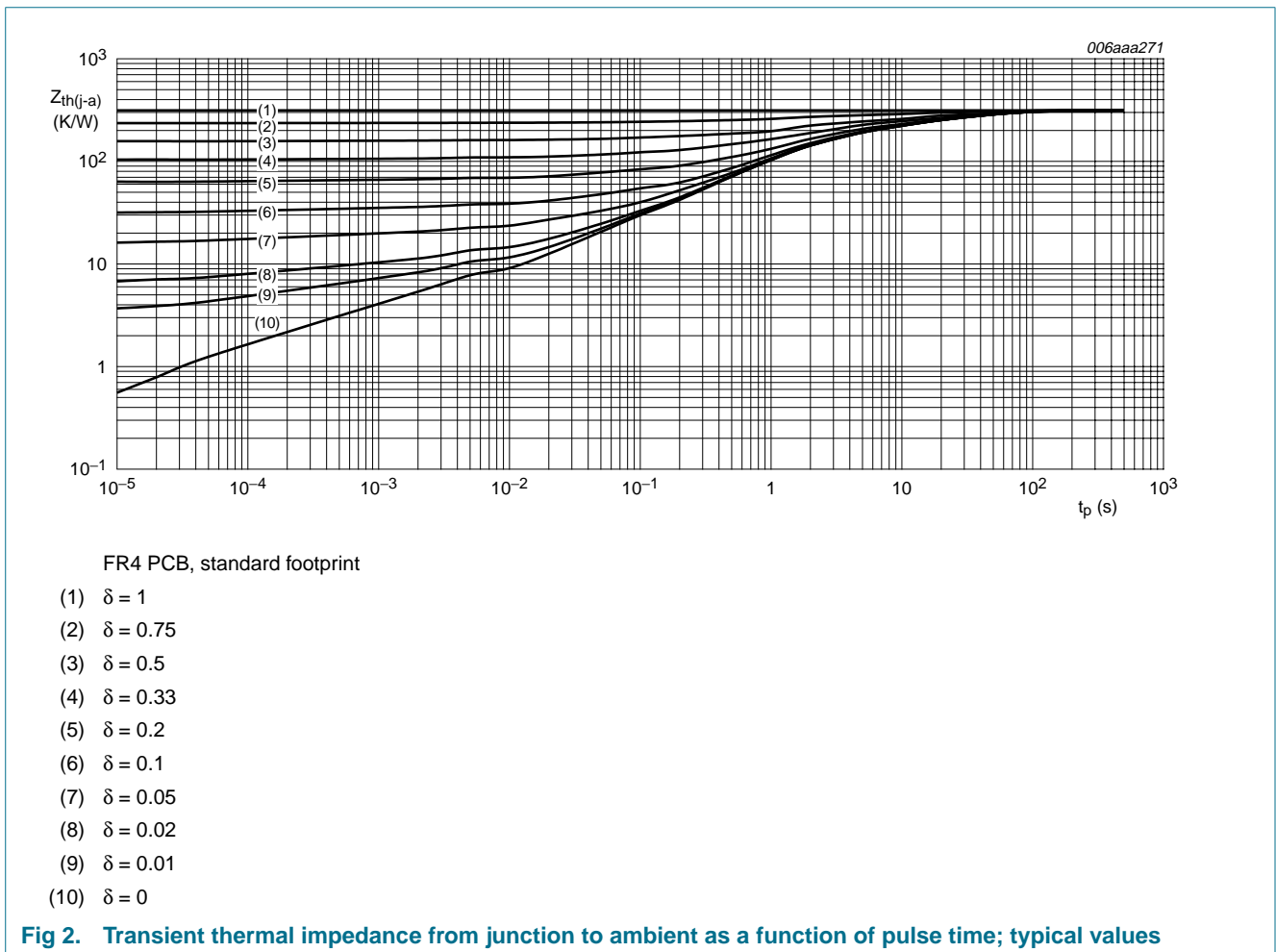


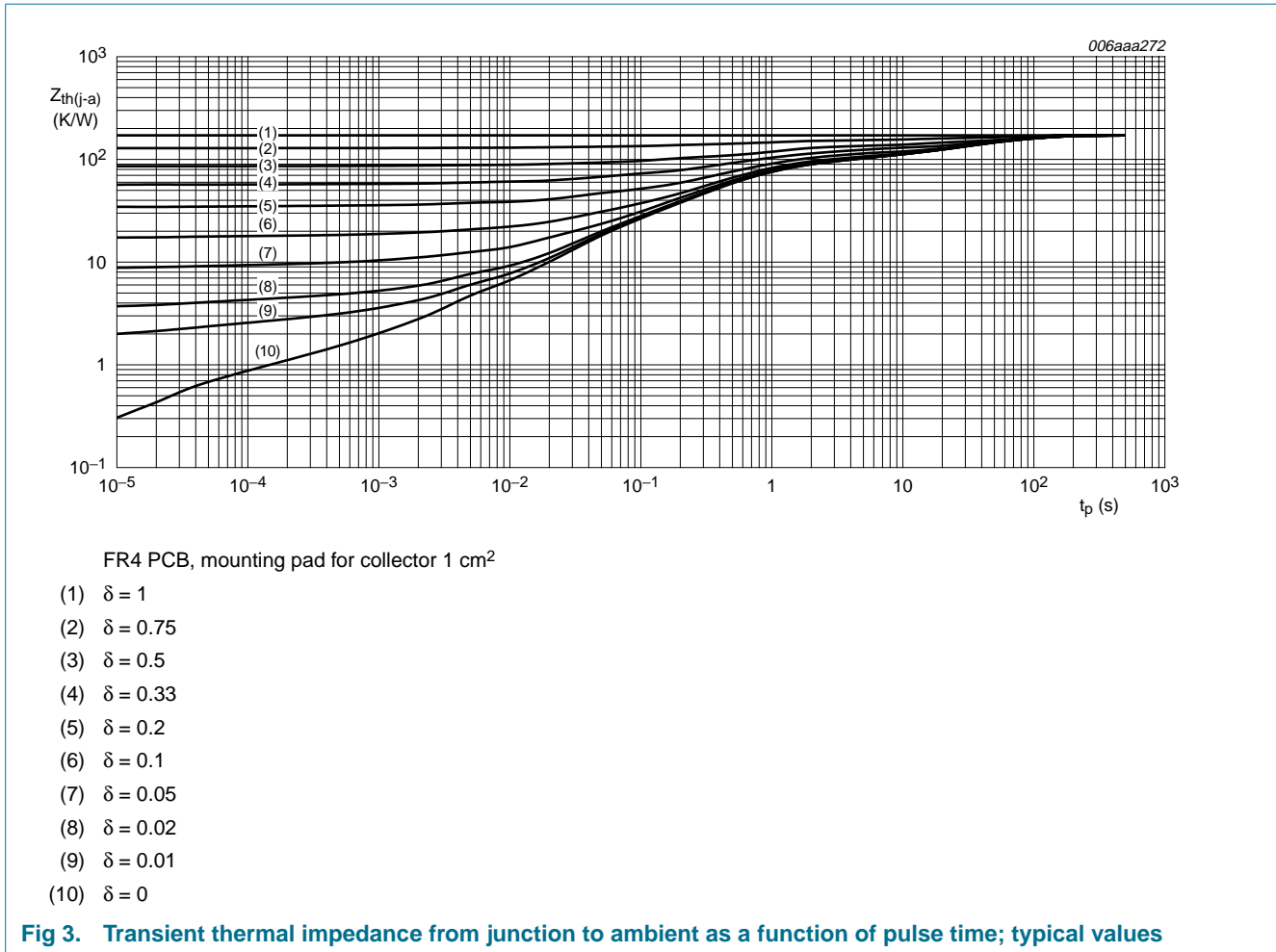
6. Thermal characteristics

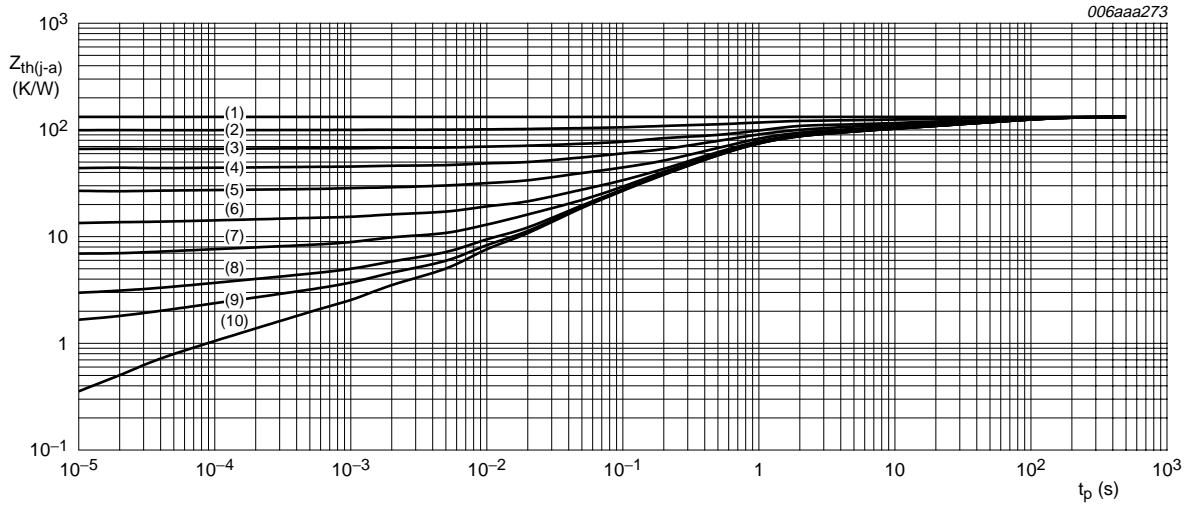
Table 6: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	350	K/W
			[2]	-	-	208	K/W
			[3]	-	-	160	K/W
			[4]	-	-	113	K/W
			[1][5]	-	-	50	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	45	K/W	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, AL₂O₃, standard footprint.
- [5] Operated under pulsed conditions: Duty cycle $\delta \leq 10\%$ and pulse width $t_p \leq 10$ ms.







FR4 PCB, mounting pad for collector 6 cm²

- (1) $\delta = 1$
- (2) $\delta = 0.75$
- (3) $\delta = 0.5$
- (4) $\delta = 0.33$
- (5) $\delta = 0.2$
- (6) $\delta = 0.1$
- (7) $\delta = 0.05$
- (8) $\delta = 0.02$
- (9) $\delta = 0.01$
- (10) $\delta = 0$

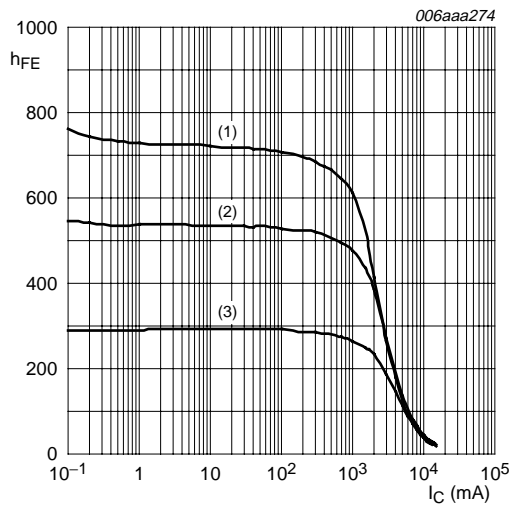
Fig 4. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

7. Characteristics

Table 7: Characteristics
 $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = 40\text{ V}; I_E = 0\text{ A}$	-	-	0.1	μA
		$V_{CB} = 40\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	50	μA
I_{CES}	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; V_{BE} = 0\text{ V}$	-	-	0.1	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	0.1	μA
h_{FE}	DC current gain	$V_{CE} = 2\text{ V}; I_C = 0.5\text{ A}$	300	-	-	
		$V_{CE} = 2\text{ V}; I_C = 1\text{ A}$	[1] 300	-	-	
		$V_{CE} = 2\text{ V}; I_C = 2\text{ A}$	[1] 250	-	-	
		$V_{CE} = 2\text{ V}; I_C = 4\text{ A}$	[1] 100	-	-	
		$V_{CE} = 2\text{ V}; I_C = 6\text{ A}$	[1] 50	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 0.5\text{ A}; I_B = 50\text{ mA}$	-	35	60	mV
		$I_C = 1\text{ A}; I_B = 50\text{ mA}$	-	65	110	mV
		$I_C = 2\text{ A}; I_B = 200\text{ mA}$	-	115	180	mV
		$I_C = 4\text{ A}; I_B = 400\text{ mA}$	[1] -	220	300	mV
		$I_C = 6\text{ A}; I_B = 600\text{ mA}$	[1] -	330	450	mV
R_{CEsat}	collector-emitter saturation resistance	$I_C = 6\text{ A}; I_B = 600\text{ mA}$	[1] -	55	75	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = 0.5\text{ A}; I_B = 50\text{ mA}$	-	0.79	0.85	V
		$I_C = 1\text{ A}; I_B = 50\text{ mA}$	-	0.81	0.9	V
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$	[1] -	0.83	1	V
		$I_C = 4\text{ A}; I_B = 400\text{ mA}$	[1] -	1.0	1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 2\text{ A}$	-	0.79	1.0	V
t_d	delay time	$V_{CC} = 10\text{ V}; I_C = 2\text{ A}; I_{Bon} = 0.1\text{ A};$ $I_{Boff} = -0.1\text{ A}$	-	12	-	ns
t_r	rise time		-	52	-	ns
t_{on}	turn-on time		-	64	-	ns
t_s	storage time		-	390	-	ns
t_f	fall time		-	120	-	ns
t_{off}	turn-off time		-	510	-	ns
f_T	transition frequency	$V_{CE} = 10\text{ V}; I_C = 0.1\text{ A};$ $f = 100\text{ MHz}$	-	150	-	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	-	30	-	pF

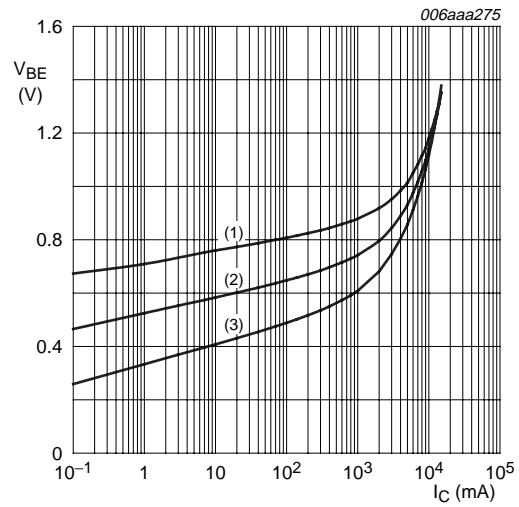
[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.



$V_{CE} = 2\text{ V}$

- (1) $T_{amb} = 100\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = -55\text{ °C}$

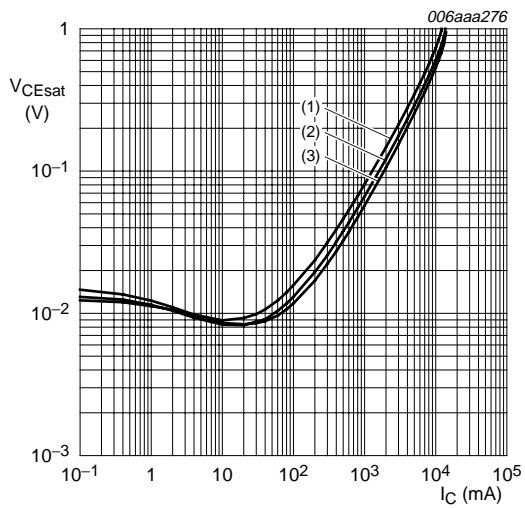
Fig 5. DC current gain as a function of collector current; typical values



$V_{CE} = 2\text{ V}$

- (1) $T_{amb} = -55\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = 100\text{ °C}$

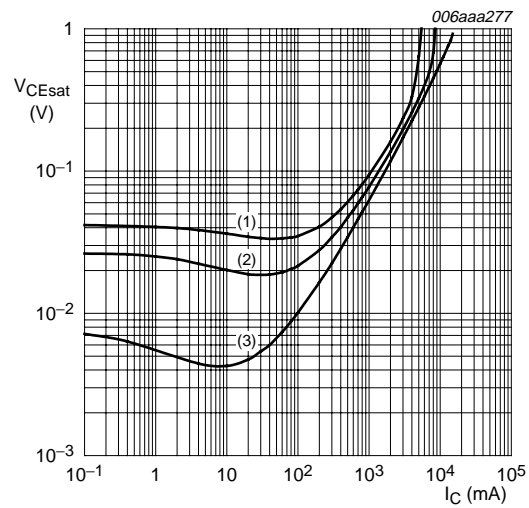
Fig 6. Base-emitter voltage as a function of collector current; typical values



$I_C/I_B = 20$

- (1) $T_{amb} = 100\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = -55\text{ °C}$

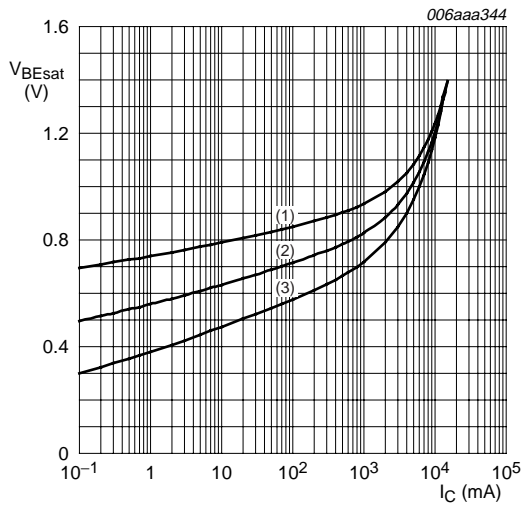
Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



$T_{amb} = 25\text{ °C}$

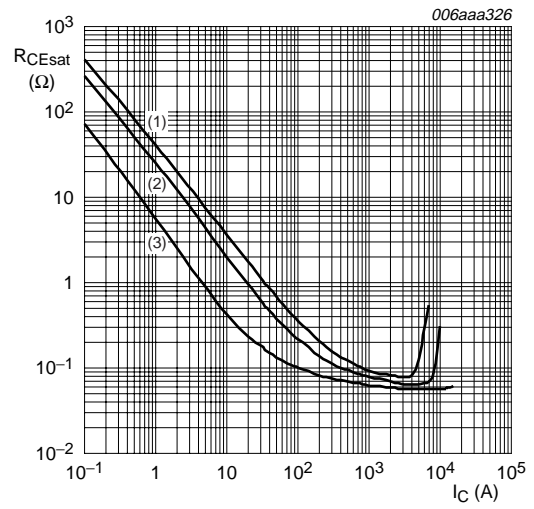
- (1) $I_C/I_B = 100$
- (2) $I_C/I_B = 50$
- (3) $I_C/I_B = 10$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



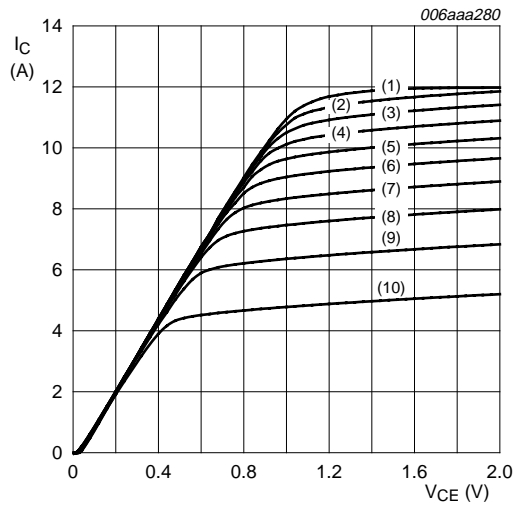
$I_C/I_B = 20$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig 9. Base-emitter saturation voltage as a function of collector current; typical values



$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

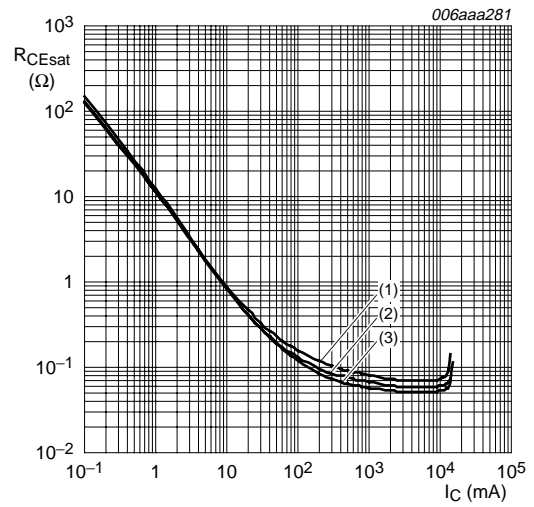
Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values



$T_{amb} = 25\text{ }^\circ\text{C}$

- (1) $I_B = 400\text{ mA}$
- (2) $I_B = 360\text{ mA}$
- (3) $I_B = 320\text{ mA}$
- (4) $I_B = 280\text{ mA}$
- (5) $I_B = 240\text{ mA}$
- (6) $I_B = 200\text{ mA}$
- (7) $I_B = 160\text{ mA}$
- (8) $I_B = 120\text{ mA}$
- (9) $I_B = 80\text{ mA}$
- (10) $I_B = 40\text{ mA}$

Fig 11. Collector current as a function of collector-emitter voltage; typical values



$I_C/I_B = 20$

- (1) $T_{amb} = 100\text{ }^\circ\text{C}$
- (2) $T_{amb} = 25\text{ }^\circ\text{C}$
- (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

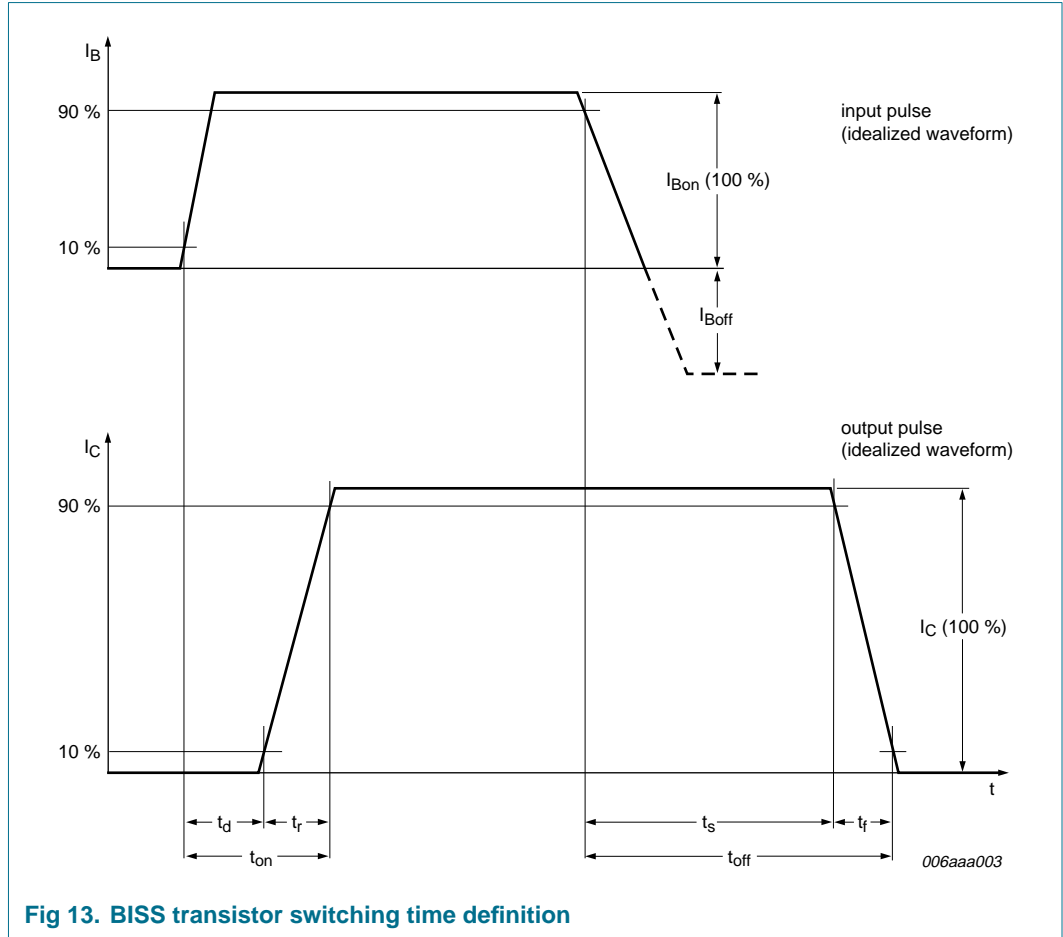


Fig 13. BISS transistor switching time definition

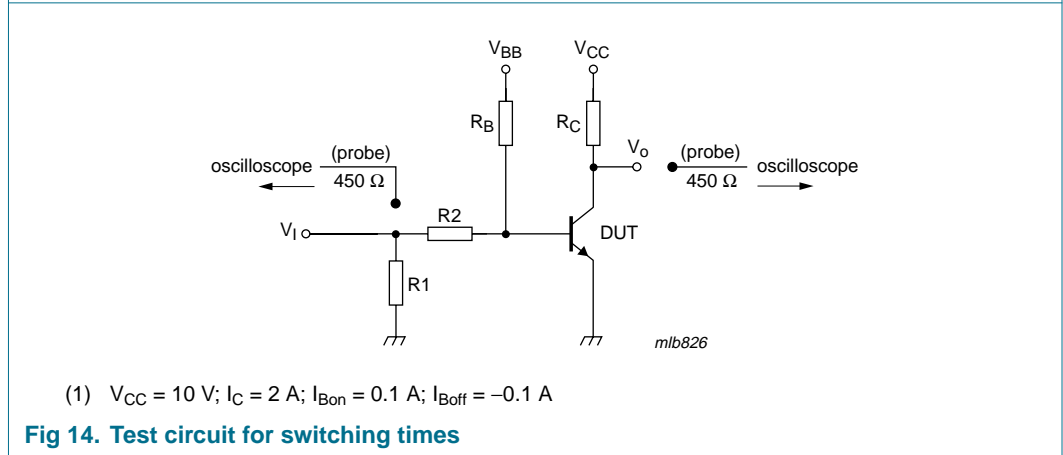


Fig 14. Test circuit for switching times

9. Package outline

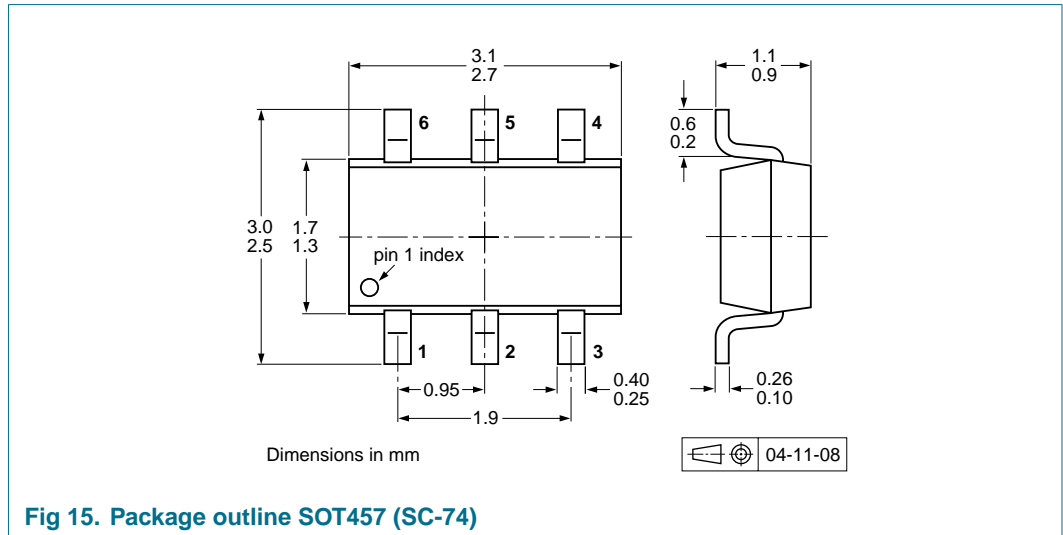


Fig 15. Package outline SOT457 (SC-74)

10. Packing information

Table 8: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing quantity		
			3000	5000	10000
PBSS302ND	SOT457	4 mm pitch, 8 mm tape and reel; T1	[2] -115	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3] -125	-	-165

[1] For further information and the availability of packing methods, see [Section 15](#).

[2] T1: normal taping

[3] T2: reverse taping



11. Revision history

Table 9: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PBSS302ND_1	20050419	Product data sheet	-	9397 750 14514	-

12. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

13. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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